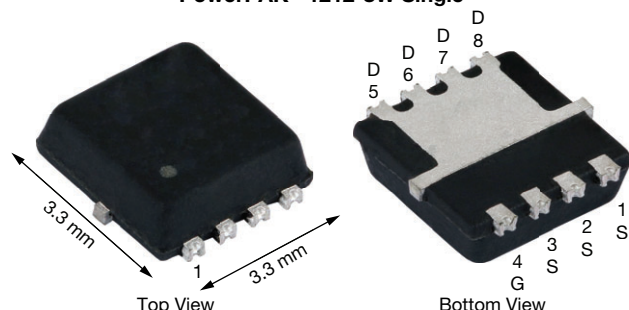


# Automotive N-Channel 30 V (D-S) 175 °C MOSFET

**PowerPAK® 1212-8W Single**

**Marking code: Q034**

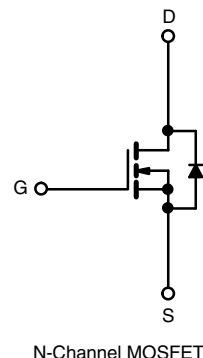
## PRODUCT SUMMARY

|                                               |                  |
|-----------------------------------------------|------------------|
| $V_{DS}$ (V)                                  | 30               |
| $R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10$ V  | 0.0085           |
| $R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5$ V | 0.0100           |
| $I_D$ (A)                                     | 16               |
| Configuration                                 | Single           |
| Package                                       | PowerPAK 1212-8W |

## FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified <sup>d</sup>
- 100 %  $R_g$  and UIS tested
- Material categorization:  
for definitions of compliance please see  
[www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

AUTOMOTIVE  
GRADE

**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**


N-Channel MOSFET

## ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

| PARAMETER                                                    |                         | SYMBOL                            | LIMIT       | UNIT |
|--------------------------------------------------------------|-------------------------|-----------------------------------|-------------|------|
| Drain-source voltage                                         |                         | V <sub>DS</sub>                   | 30          | V    |
| Gate-source voltage                                          |                         | V <sub>GS</sub>                   | ± 20        |      |
| Continuous drain current <sup>a</sup>                        | T <sub>C</sub> = 25 °C  | I <sub>D</sub>                    | 16          | A    |
|                                                              | T <sub>C</sub> = 125 °C |                                   | 16          |      |
| Continuous source current (diode conduction) <sup>a</sup>    |                         | I <sub>S</sub>                    | 16          |      |
| Pulsed drain current <sup>b</sup>                            |                         | I <sub>DM</sub>                   | 64          |      |
| Single pulse avalanche current                               | L = 0.1 mH              | I <sub>AS</sub>                   | 31          |      |
| Single pulse avalanche energy                                |                         | E <sub>AS</sub>                   | 48          | mJ   |
| Maximum power dissipation <sup>b</sup>                       | T <sub>C</sub> = 25 °C  | P <sub>D</sub>                    | 62          | W    |
|                                                              | T <sub>C</sub> = 125 °C |                                   | 20          |      |
| Operating junction and storage temperature range             |                         | T <sub>J</sub> , T <sub>stg</sub> | -55 to +175 | °C   |
| Soldering recommendations (peak temperature) <sup>e, f</sup> |                         |                                   | 260         |      |

## THERMAL RESISTANCE RATINGS

| PARAMETER                | SYMBOL     | LIMIT | UNIT |
|--------------------------|------------|-------|------|
| Junction-to-ambient      | $R_{thJA}$ | 81    | °C/W |
| Junction-to-case (drain) | $R_{thJC}$ | 2.4   |      |

### Notes

- Package limited
- Pulse test; pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2$  %
- When mounted on 1" square PCB (FR4 material)
- Parametric verification ongoing
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK 1212-8W is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

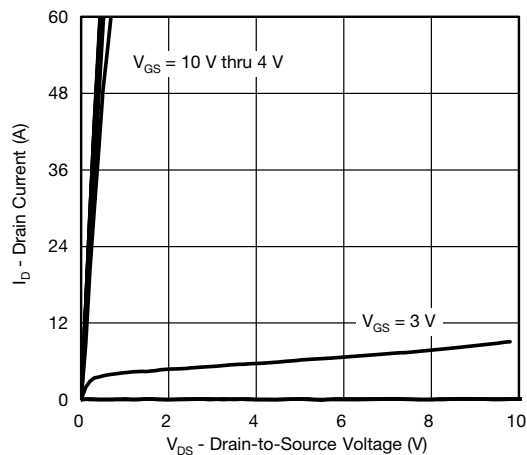
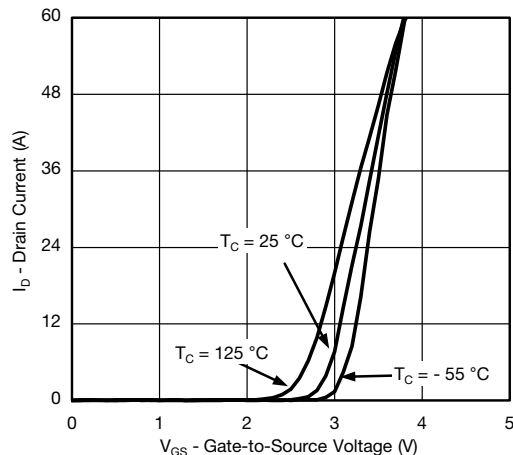
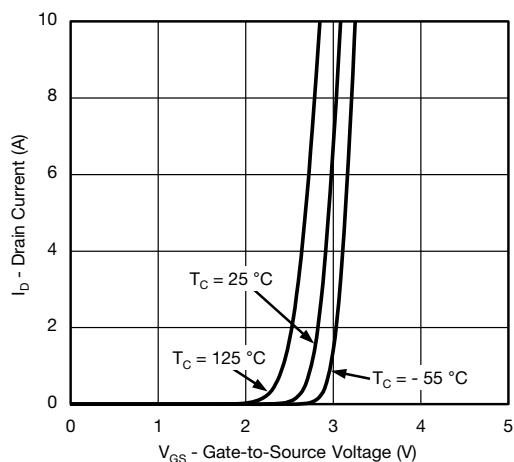
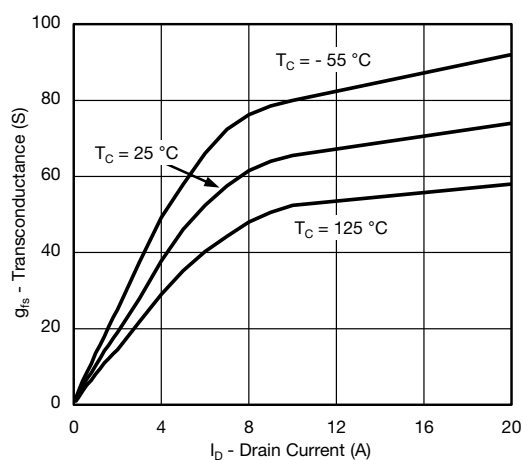
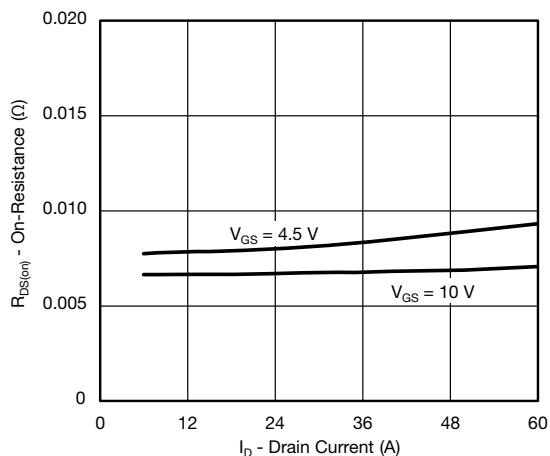
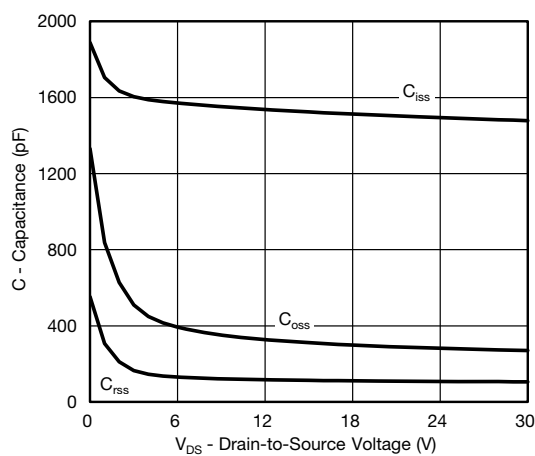


| SPECIFICATIONS (T <sub>C</sub> = 25 °C, unless otherwise noted) |                     |                                                                                                                     |                                                  |      |        |        |      |
|-----------------------------------------------------------------|---------------------|---------------------------------------------------------------------------------------------------------------------|--------------------------------------------------|------|--------|--------|------|
| PARAMETER                                                       | SYMBOL              | TEST CONDITIONS                                                                                                     |                                                  | MIN. | TYP.   | MAX.   | UNIT |
| Static                                                          |                     |                                                                                                                     |                                                  |      |        |        |      |
| Drain-source breakdown voltage                                  | V <sub>DS</sub>     | V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA                                                                        |                                                  | 30   | -      | -      | V    |
| Gate-source threshold voltage                                   | V <sub>GS(th)</sub> | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                         |                                                  | 1.5  | 2.0    | 2.5    |      |
| Gate-source leakage                                             | I <sub>GSS</sub>    | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V                                                                     |                                                  | -    | -      | ± 100  | nA   |
| Zero gate voltage drain current                                 | I <sub>DSS</sub>    | V <sub>GS</sub> = 0 V                                                                                               | V <sub>DS</sub> = 30 V                           | -    | -      | 1      | μA   |
|                                                                 |                     | V <sub>GS</sub> = 0 V                                                                                               | V <sub>DS</sub> = 30 V, T <sub>J</sub> = 125 °C  | -    | -      | 50     |      |
|                                                                 |                     | V <sub>GS</sub> = 0 V                                                                                               | V <sub>DS</sub> = 30 V, T <sub>J</sub> = 175 °C  | -    | -      | 150    |      |
| On-state drain current <sup>a</sup>                             | I <sub>D(on)</sub>  | V <sub>GS</sub> = 10 V                                                                                              | V <sub>DS</sub> ≥ 5 V                            | 20   | -      | -      | A    |
| Drain-source on-state resistance <sup>a</sup>                   | R <sub>DS(on)</sub> | V <sub>GS</sub> = 10 V                                                                                              | I <sub>D</sub> = 16.4 A                          | -    | 0.0070 | 0.0085 | Ω    |
|                                                                 |                     | V <sub>GS</sub> = 10 V                                                                                              | I <sub>D</sub> = 16.4 A, T <sub>J</sub> = 125 °C | -    | -      | 0.0135 |      |
|                                                                 |                     | V <sub>GS</sub> = 10 V                                                                                              | I <sub>D</sub> = 16.4 A, T <sub>J</sub> = 175 °C | -    | -      | 0.0160 |      |
|                                                                 |                     | V <sub>GS</sub> = 4.5 V                                                                                             | I <sub>D</sub> = 16.4 A                          | -    | 0.0080 | 0.0100 |      |
| Forward transconductance <sup>b</sup>                           | g <sub>fs</sub>     | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 16.4 A                                                                     |                                                  | -    | 70     | -      | S    |
| Dynamic <sup>b</sup>                                            |                     |                                                                                                                     |                                                  |      |        |        |      |
| Input capacitance                                               | C <sub>iss</sub>    | V <sub>GS</sub> = 0 V                                                                                               | V <sub>DS</sub> = 25 V, f = 1 MHz                | -    | 1492   | 1865   | pF   |
| Output capacitance                                              | C <sub>oss</sub>    |                                                                                                                     |                                                  | -    | 280    | 350    |      |
| Reverse transfer capacitance                                    | C <sub>rss</sub>    |                                                                                                                     |                                                  | -    | 108    | 135    |      |
| Total gate charge <sup>c</sup>                                  | Q <sub>g</sub>      | V <sub>GS</sub> = 10 V                                                                                              | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A    | -    | 26     | 39     | nC   |
| Gate-source charge <sup>c</sup>                                 | Q <sub>gs</sub>     |                                                                                                                     |                                                  | -    | 4.7    | -      |      |
| Gate-drain charge <sup>c</sup>                                  | Q <sub>gd</sub>     |                                                                                                                     |                                                  | -    | 4.3    | -      |      |
| Gate resistance                                                 | R <sub>g</sub>      | f = 1 MHz                                                                                                           |                                                  | 5    | 10     | 20     | Ω    |
| Turn-on delay time <sup>c</sup>                                 | t <sub>d(on)</sub>  | V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω<br>I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω |                                                  | -    | 7      | 11     | ns   |
| Rise time <sup>c</sup>                                          | t <sub>r</sub>      |                                                                                                                     |                                                  | -    | 21     | 32     |      |
| Turn-off delay time <sup>c</sup>                                | t <sub>d(off)</sub> |                                                                                                                     |                                                  | -    | 49     | 74     |      |
| Fall Time <sup>c</sup>                                          | t <sub>f</sub>      |                                                                                                                     |                                                  | -    | 18     | 27     |      |
| Source-Drain Diode Ratings and Characteristics <sup>b</sup>     |                     |                                                                                                                     |                                                  |      |        |        |      |
| Pulsed current <sup>a</sup>                                     | I <sub>SM</sub>     |                                                                                                                     |                                                  | -    | -      | 64     | A    |
| Forward voltage                                                 | V <sub>SD</sub>     | I <sub>F</sub> = 15 A, V <sub>GS</sub> = 0                                                                          |                                                  | -    | 0.82   | 1.2    | V    |

**Notes**

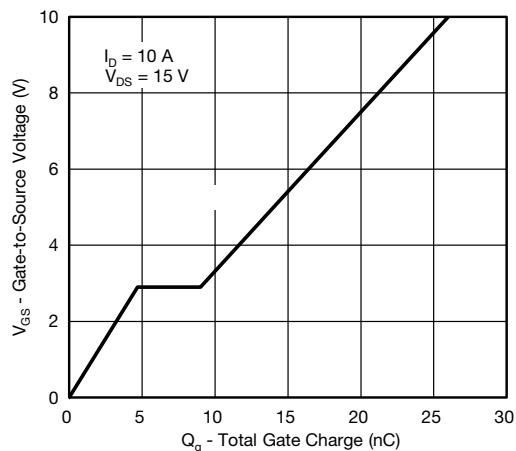
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing  
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

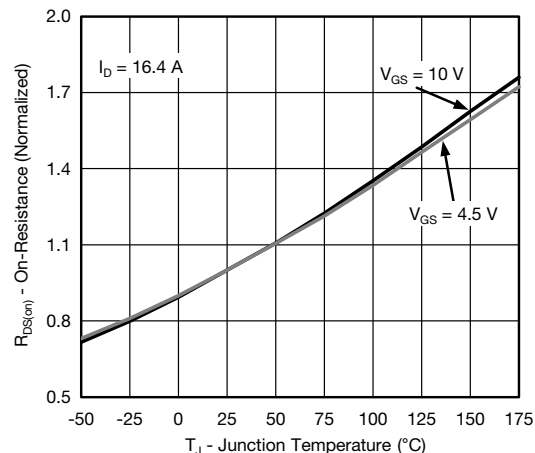
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

**Output Characteristics**

**Transfer Characteristics**

**Transfer Characteristics**

**Transconductance**

**On-Resistance vs. Drain Current**

**Capacitance**



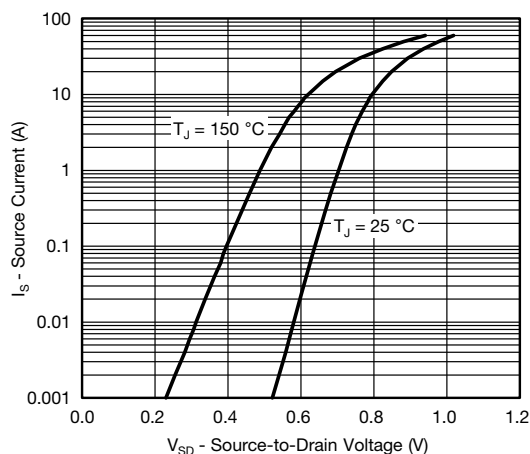
**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)



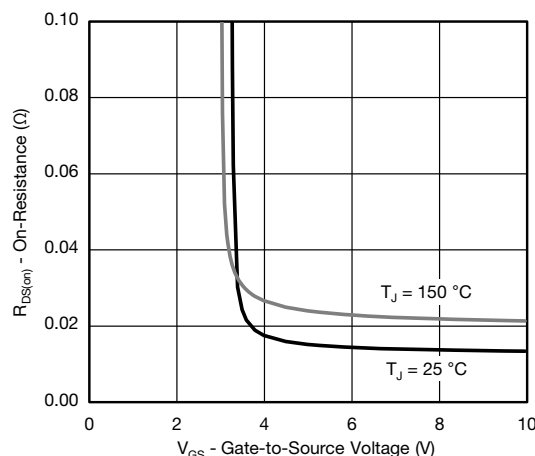
Gate Charge



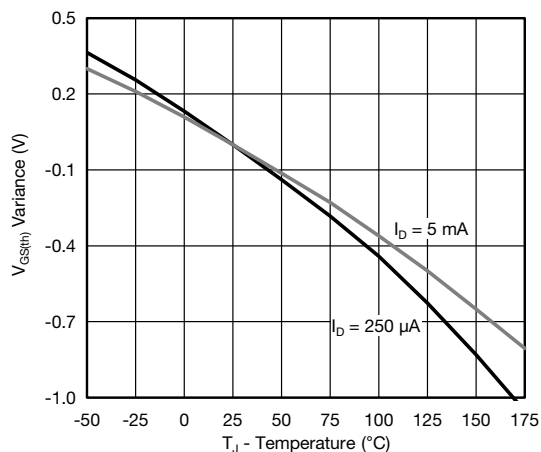
On-Resistance vs. Junction Temperature



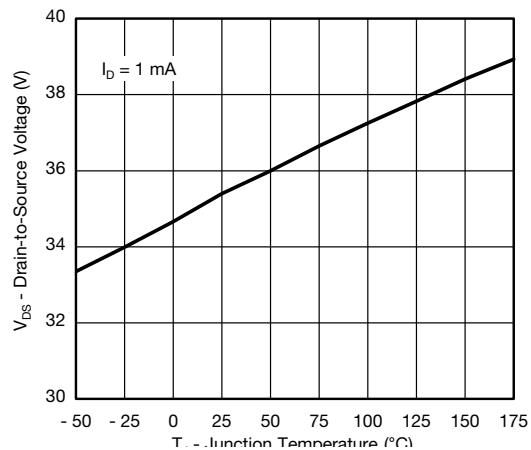
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



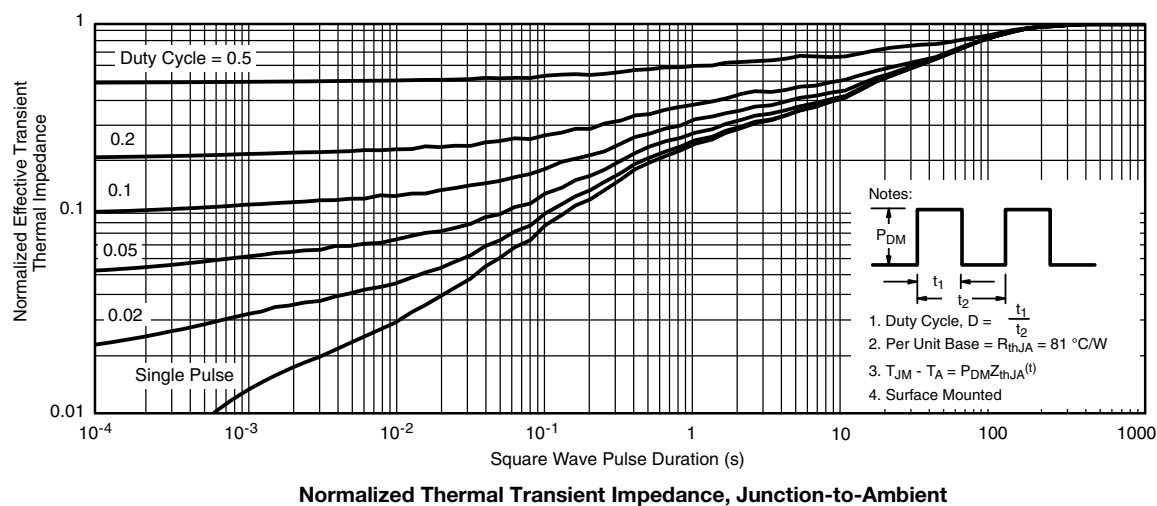
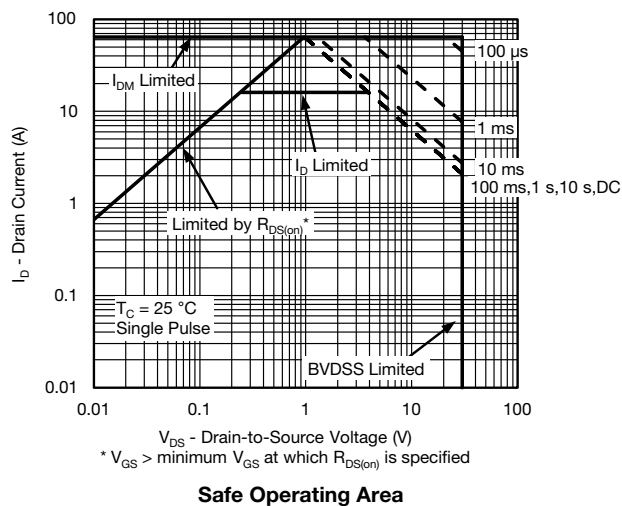
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

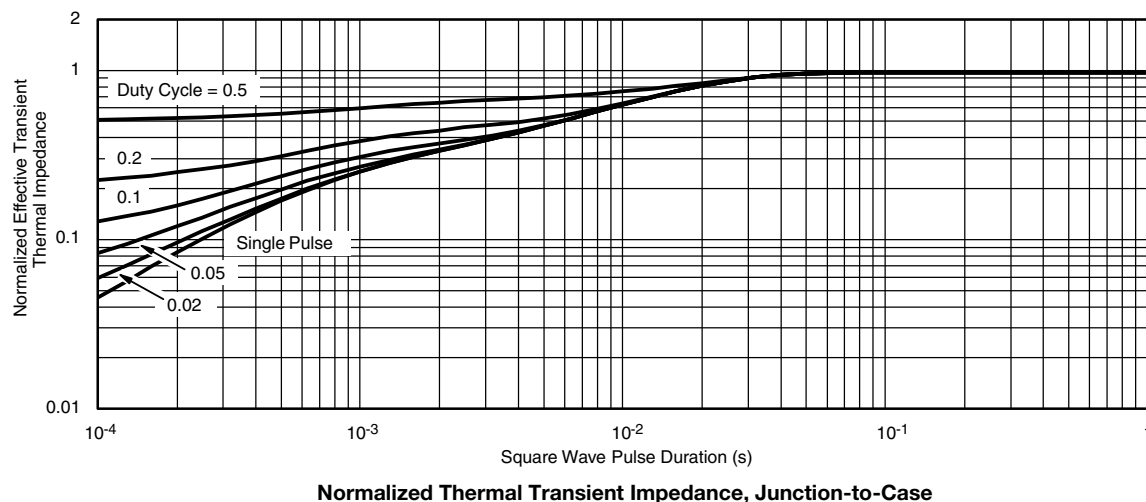


**THERMAL RATINGS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)





**THERMAL RATINGS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)



**Note**

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient ( $25\text{ }^{\circ}\text{C}$ )
  - Normalized Transient Thermal Impedance Junction-to-Case ( $25\text{ }^{\circ}\text{C}$ )are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?75543](http://www.vishay.com/ppg?75543).

**PowerPAK® 1212-8 and PowerPAK 1212-8W**

Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK 1212-8 and PowerPAK 1212-8W packages:

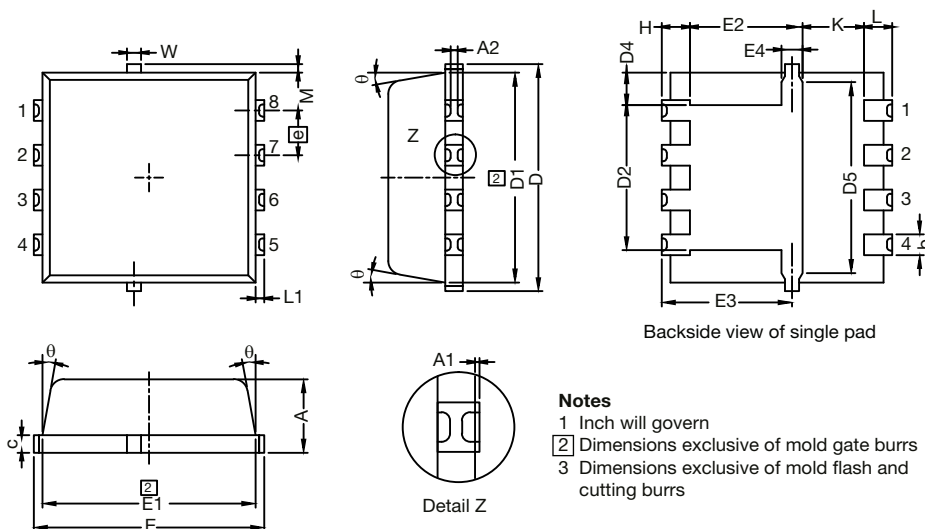
| DATASHEET PART NUMBER | OLD ORDERING CODE <sup>a</sup> | NEW ORDERING CODE |
|-----------------------|--------------------------------|-------------------|
| SQ7414AEN             | SQ7414AEN-T1-GE3               | SQ7414AEN-T1_GE3  |
| SQ7414AENW            | -                              | SQ7414AENW-T1_GE3 |
| SQ7415AEN             | SQ7415AEN-T1-GE3               | SQ7415AEN-T1_GE3  |
| SQ7415AENW            | -                              | SQ7415AENW-T1_GE3 |
| SQS401EN              | SQS401EN-T1-GE3                | SQS401EN-T1_GE3   |
| SQS401ENW             | -                              | SQS401ENW-T1_GE3  |
| SQS405EN              | SQS405EN-T1-GE3                | SQS405EN-T1_GE3   |
| SQS405ENW             | -                              | SQS405ENW-T1_GE3  |
| SQS420EN              | SQS420EN-T1-GE3                | SQS420EN-T1_GE3   |
| SQS423EN              | SQS423EN-T1-GE3                | SQS423EN-T1_GE3   |
| SQS460EN              | SQS460EN-T1-GE3                | SQS460EN-T1_GE3   |
| SQS462EN              | SQS462EN-T1-GE3                | SQS462EN-T1_GE3   |
| SQS482EN              | SQS482EN-T1-GE3                | SQS482EN-T1_GE3   |
| SQS484EN              | SQS484EN-T1-GE3                | SQS484EN-T1_GE3   |
| SQS490EN              | SQS490EN-T1-GE3                | SQS490EN-T1_GE3   |
| SQS840EN              | SQS840EN-T1-GE3                | SQS840EN-T1_GE3   |
| SQS850EN              | SQS850EN-T1-GE3                | SQS850EN-T1_GE3   |

**Note**

a. Old ordering code is obsolete and no longer valid for new orders



## PowerPAK® 1212-8W Case Outline



| DIM.                            | MILLIMETERS |      |      | INCHES      |       |       |
|---------------------------------|-------------|------|------|-------------|-------|-------|
|                                 | MIN.        | NOM. | MAX. | MIN.        | NOM.  | MAX.  |
| A                               | 0.97        | 1.04 | 1.12 | 0.038       | 0.041 | 0.044 |
| A1                              | 0           | -    | 0.05 | 0           | -     | 0.002 |
| A2                              | 0           | -    | 0.13 | 0           | -     | 0.005 |
| b                               | 0.23        | 0.30 | 0.41 | 0.009       | 0.012 | 0.016 |
| c                               | 0.23        | 0.28 | 0.33 | 0.009       | 0.011 | 0.013 |
| D                               | 3.20        | 3.30 | 3.40 | 0.126       | 0.130 | 0.134 |
| D1                              | 2.95        | 3.05 | 3.15 | 0.116       | 0.120 | 0.124 |
| D2                              | 1.98        | 2.11 | 2.24 | 0.078       | 0.083 | 0.088 |
| D4                              | 0.47 typ.   |      |      | 0.0185 typ. |       |       |
| D5                              | 2.3 typ.    |      |      | 0.090 typ.  |       |       |
| E                               | 3.20        | 3.30 | 3.40 | 0.126       | 0.130 | 0.134 |
| E1                              | 2.95        | 3.05 | 3.15 | 0.116       | 0.120 | 0.124 |
| E2                              | 1.47        | 1.60 | 1.73 | 0.058       | 0.063 | 0.068 |
| E3                              | 1.75        | 1.85 | 1.98 | 0.069       | 0.073 | 0.078 |
| E4                              | 0.34 typ.   |      |      | 0.013 typ.  |       |       |
| e                               | 0.65 BSC.   |      |      | 0.026 BSC   |       |       |
| K                               | 0.86 typ.   |      |      | 0.034 typ.  |       |       |
| H                               | 0.30        | 0.41 | 0.51 | 0.012       | 0.016 | 0.020 |
| L                               | 0.30        | 0.43 | 0.56 | 0.012       | 0.017 | 0.022 |
| L1                              | 0.06        | 0.13 | 0.20 | 0.002       | 0.005 | 0.008 |
| θ                               | 0°          | -    | 12°  | 0°          | -     | 12°   |
| W                               | 0.15        | 0.25 | 0.36 | 0.006       | 0.010 | 0.014 |
| M                               | 0.125 typ.  |      |      | 0.005 typ.  |       |       |
| ECN: C15-1530-Rev. B, 16-Nov-15 |             |      |      |             |       |       |
| DWG: 6032                       |             |      |      |             |       |       |





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